



KEY FEATURES



10BB Half-cut Cell Technology

New circuit design, lower internal current, lower R_s loss
Ga doped wafer, attenuation $< 2\%$ (1st year) / $\leq 0.45\%$ (Linear)



Industry Leading High Yield

Bifacial PERC cell technology,
5%-25% more yield depends on different conditions



Excellent Anti-PID Performance

2 times of industry standard Anti-PID test



ELECTRICAL CHARACTERISTICS

	20.40	20.60	20.80	21.00	21.20

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REAR SIDE POWER GAIN(REFER TO Td(S)p840 Tdc30614(OTd(96ot\$TDE/4SE/484nP DE/4SE/4dc306Td())Tdc306T

	5%	10%	15%	20%	25%
	515	539	564	588	613
	38.02	38.02	38.02	38.02	38.02
	13.53	14.18	14.82	15.47	16.11
	45.31	45.31	45.31	45.31	45.31
	14.47	15.16	15.85	16.54	17.23